L Numbe			DB	Time stamp
-	0	("ferroelectric adj memory").PN.	USPAT;	2002/10/03 08:31
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	0	("insulat\$ and substrate and contact adj	USPAT;	2002/10/03 08:33
-		hole and (burry buried)").PN.	US-PGPUB;	2002/10/03 00:33
		note and (burly burled) /	EPO; JPO;	
	- 6		DERWENT;	
			IBM TDB	
_	3514	ferroelectric adj memory	USPAT;	2002/10/03 08:34
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/10/00 10 04
-	0	insulat\$3 and substrate and contact adj	USPAT;	2002/10/08 12:24
		hole and (burry and burried)	US-PGPUB;	
			EPO; JPO; DERWENT;	
!			IBM TDB	
_	0	insulat\$3 and substrate and (burry and	USPAT;	2002/10/03 08:36
		burried)	US-PGPUB;	-002, 10, 00 00.50
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	337972	insulat\$3 and substrate	USPAT;	2002/10/03 08:36
			US-PGPUB;	
			EPO; JPO;	
!			DERWENT;	İ
			IBM_TDB	
-	1091		USPAT;	2002/10/03 08:36
		and substrate)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	923	((ferroelectric adj memory) and (insulat\$3	IBM_TDB USPAT;	2002/10/03 08:37
-	923	and substrate)) and capacitor	US-PGPUB;	2002/10/03 08.3/
		and Substrate // and Capacitor	EPO; JPO;	
			DERWENT;	
			IBM TDB	
	330	(((ferroelectric adj memory) and	USPĀT;	2003/03/04 09:56
	9.1	(insulat\$3 and substrate)) and	US-PGPUB;	
		capacitor) and contact adj hole	EPO; JPO;	
			DERWENT;	
	- 6		IBM_TDB	
-	3	((((ferroelectric adj memory) and	USPAT;	2002/10/08 12:13
		(insulat\$3 and substrate)) and	US-PGPUB;	
		capacitor) and contact adj hole) and	EPO; JPO;	
	3	blocking adj layer	DERWENT;	
_	12043	kwon.in.	IBM_TDB USPAT;	2002/10/03 08:53
_	12043	NWOII. III.	US-PGPUB;	2002/10/03 00:33
			EPO; JPO;	
			DERWENT;	
	110-11		IBM TDB	
_	. 12043	kwon-s.in.	USPAT;	2002/10/03 08:53
			US-PGPUB;	
			EPO; JPO;	
: 			DERWENT;	
			IBM_TDB	
-	134	kwon-s-y.in.	USPAT;	2002/10/03 08:54
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		1	IBM TDB	
	101	Duran a set in	HCDAM.	2002/10/02 00:00
_	134	'kwon, s y'.in.	USPAT;	2002/10/03 09:22
-	134	'kwon, s y'.in.	US-PGPUB;	2002/10/03 09:22
-	134	'kwon, s y'.in.		2002/10/03 09:22

_	2	6162649.pn.	USPAT; US-PGPUB;	2002/10/03 09:23
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	2	6379977.pn.	USPAT; US-PGPUB;	2002/10/03 09:23
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	2	6210979.pn.	USPAT; US-PGPUB;	2002/10/03 09:24
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	0000/10/00 10 04
-	4.3	insulat\$3 and substrate and contact adj hole and (burry or burried)	USPAT; US-PGPUB;	2002/10/08 12:24
		note and (bully of bullled)	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	((438/3,253,254,238,396).CCLS.) and (insulat\$3 and substrate and contact adj	USPAT; US-PGPUB;	2002/10/08 12:25
	1	hole and (burry or burried))	EPO; JPO;	
		,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	DERWENT;	
			IBM_TDB	
- 1 11	1		USPAT;	2002/10/08 12:25
		(insulat\$3 and substrate and contact adj hole and (burry or burried))	US-PGPUB; EPO; JPO;	
		note and (bully of bullled))	DERWENT;	
			IBM_TDB	
-	27		USPAT;	2002/10/08 12:31
		buried near3 contact) and ferroelectric)	US-PGPUB;	
		and contact adj hole) and ((silicon adj oxynitride) or (silicon adj nitride))	EPO; JPO; DERWENT;	
		(01111111111111111111111111111111111111	IBM TDB	
-	45		USPAT;	2002/10/08 12:40
		near3 contact) and ferroelectric) and contact adj hole	US-PGPUB; EPO; JPO;	
		Contact adj note	DERWENT;	
			IBM TDB	
-	54	(((257/295,298,310,532).CCLS.) and buried	USPĀT;	2002/10/08 17:02
		near3 contact) and ferroelectric	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
-	124	((257/295,298,310,532).CCLS.) and buried	USPĀT;	2002/10/08 12:41
		near3 contact	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
, -	2641	(257/295,298,310,532).CCLS.	USPĀT;	2002/10/08 12:43
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
0- 11	4442	(257/295,296,298,310,532).CCLS.	USPAT;	2002/10/08 16:05
			US-PGPUB;	
			EPO; JPO;	1
			DERWENT; IBM TDB	
-	5525	(438/3,253,254,238,396).CCLS.	USPĀT;	2002/10/08 12:46
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	2	5411911.pn.	USPAT;	2002/10/08 16:05
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	L

-	29	(((257/295,298,310,532).CCLS.) and buried near3 contact) and ferroelectric and plug	USPAT; US-PGPUB;	2003/03/03 09:25
		with (tungsten 'W')	EPO; JPO; DERWENT; IBM TDB	
-	2	6144052.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/10/09 10:39
-	2	6316803.pn.	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/10/09 10:39
_	150211	"12" and ((silicon adj oxynitride) "SiON") or ((silicon adj nitride) "SiN")	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/03 09:25
-	153281	((silicon adj oxynitride) "SiON") or ((silicon adj nitride) "SiN")	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/03/03 09:25
-	22	((silicon adj nitride) "SiN")) and (((257/295,298,310,532).CCLS.) and buried near3 contact) and ferroelectric and plug	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/04 09:43
-	1	with (tungsten 'W') 09/947378	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/03 15:37
_	17	"DRAM" and (((silicon adj oxynitride) "SiON") or ((silicon adj nitride) "SiN")) and (((257/295,298,310,532).CCLS.) and buried near3 contact) and ferroelectric	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/04 09:43
_	17	and plug with (tungsten 'W')	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 09:59
_	2040	with (tungsten 'W')	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/04 10:28
_	1	("DRAM" and capacitor and (((silicon adjoxynitride) "SiON") or ((silicon adjnitride) "SiN")) and (((257/295,298,310,532).CCLS.) and buried near3 contact) and ferroelectric and plug with (tungsten 'W')) and (((blocking adjlayer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj oxinitride) "SiOn" SiN))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/04 09:54
-	488		USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/04 09:55
-	370	("DRAM" and ((((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj oxinitride) "SiOn" SiN)))) and capacitor	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/04 09:55

			(/UDDAMU and ///blacking add layer) /atch	USPAT;	2003/03/04	00.56
-		4	(("DRAM" and ((((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride)	US-PGPUB;	2003/03/04	09.50
			(silicon adj oxinitride) "SiOn" SiN))))	EPO; JPO;		
			and capacitor) and (((ferroelectric adj	DERWENT;		
			memory) and (insulat\$3 and substrate))	IBM TDB		
			and capacitor) and contact adj hole	_		
-		4	"FeRAM" and capacitor and (((silicon adj	USPAT;	2003/03/04	10:00
			oxynitride) "SiON") or ((silicon adj	US-PGPUB;	1	
			nitride) "SiN")) and	EPO; JPO;		
			(((257/295,298,310,532).CCLS.) and buried	DERWENT;	1	
			near3 contact) and ferroelectric and plug	IBM_TDB		
		4	with (tungsten 'W')	USPAT;	2003/03/04	10.01
-		4	("FeRAM" and capacitor and (((silicon adjoxynitride) "SiON") or ((silicon adj	US-PGPUB;	2003/03/04	10.01
			nitride) "SiN")) and	EPO; JPO;		
			(((257/295,298,310,532).CCLS.) and buried	DERWENT;		
			near3 contact) and ferroelectric and plug	IBM TDB		
			with (tungsten 'W')) not ((("DRAM" and	15155		
			((((blocking adj layer) (etch adj stop))			
			near9 ((silicon adj nitride) (silicon adj			
			oxinitride) "SiOn" SiN)))) and capacitor)			
			and (((ferroelectric adj memory) and			
			(insulat\$3 and substrate)) and			
			capacitor) and contact adj hole)			
		886	"FeRam"	USPAT;	2003/03/04	10:01
				US-PGPUB;		
				EPO; JPO;		
				DERWENT;		
		10	WE-Damil and ///blacking add lawary (atch	IBM_TDB USPAT;	2003/03/04	10.02
_	ĺ	10	"FeRam" and ((((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride)	US-PGPUB;	2003/03/04	10.02
	V V		(silicon adj oxinitride) "SiOn" SiN)))	EPO; JPO;		
	1		(Silicon adj Oximicilde) Sion Sin///	DERWENT;		
				IBM TDB		
_	İ	2186	(((blocking adj layer) (etch adj stop))	USPAT;	2003/03/04	10:30
			near9 ((silicon adj nitride) (silicon adj	US-PGPUB;		
			oxinitride) (aluminum adj oxide) "SiOn"	EPO; JPO;	1	
			"Sin" "AlO"))	DERWENT;		
				IBM_TDB		
-	14	10	((((blocking adj layer) (etch adj stop))	USPAT;	2003/03/04	10:34
			near9 ((silicon adj nitride) (silicon adj	US-PGPUB;		
			oxinitride) (aluminum adj oxide) "SiOn"	EPO; JPO;	1	
			"SiN" "AlO"))) and feram	DERWENT;		
	-	•	11.10.2 12.10.10.10.10.10.10.10.10.10.10.10.10.10.	IBM_TDB	0000 (00 (04	10 24
		U	(((((blocking adj layer) (etch adj stop))	USPAT;	2003/03/04	10:34
			near9 ((silicon adj nitride) (silicon adj oxinitride) (aluminum adj oxide) "SiOn"	US-PGPUB; EPO; JPO;		
			"SiN" "AlO"))) and feram) not (((blocking	DERWENT;		
			adj layer) (etch adj stop)) near9	IBM TDB		
			((silicon adj nitride) (silicon adj	15.1_155	1	
	1		oxinitride) (aluminum adj oxide) "SiOn"		1	
			"SiN" "AlO")))			
		503	((((blocking adj layer) (etch adj stop))	USPAT;	2003/03/04	10:35
_			near9 ((silicon adj nitride) (silicon adj	US-PGPUB;		
-				EDO: TDO:		
			oxinitride) (aluminum adj oxide) "SiOn"	EPO; JPO;		
				DERWENT;		
			oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO"))) and dram	DERWENT; IBM_TDB		
_		378	<pre>oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO"))) and dram (((((blocking adj layer) (etch adj stop))</pre>	DERWENT; IBM_TDB USPAT;	2003/03/04	15:23
-		378	<pre>oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO"))) and dram (((((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj</pre>	DERWENT; IBM_TDB USPAT; US-PGPUB;	2003/03/04	15:23
-		378	oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO"))) and dram (((((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj oxinitride) (aluminum adj oxide) "SiOn"	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/03/04	15:23
-		378	<pre>oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO"))) and dram (((((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj</pre>	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/03/04	15:23
-			oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO"))) and dram (((((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO"))) and dram) and capacitor	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB		
-		378	<pre>oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO"))) and dram (((((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO"))) and dram) and capacitor ((((((blocking adj layer) (etch adj stop)))</pre>	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;	2003/03/04	
-			oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO"))) and dram (((((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO"))) and dram) and capacitor ((((((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB;		
-			<pre>oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO"))) and dram (((((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO"))) and dram) and capacitor ((((((blocking adj layer) (etch adj stop)))</pre>	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB USPAT;		

· -	29	(((((blocking adj layer) (etch adj stop))	USPAT;	2003/03/04 14:30
j		with ((silicon adj nitride) (silicon adj	US-PGPUB;	
		oxinitride) (aluminum adj oxide) "SiOn"	EPO; JPO;	
		"SiN" "AlO"))) and dram) and capacitor)	DERWENT;	!
		and ferroelectric	IBM_TDB	İ
-	2	("5891799").PN.	USPAT;	2003/03/05 08:43
!			US-PGPUB;	<u> </u>
			EPO; JPO;	
			DERWENT;	1
			IBM_TDB	
-	2	("6329680").PN.	USPAT;	2003/03/05 09:19
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	1
			IBM_TDB	0000/00/05 10 10
-	4	(("6251726") or ("5976977")).PN.	USPAT;	2003/03/05 10:12
			US-PGPUB;	
			EPO; JPO;	
ĺ			DERWENT;	
		(M.CO. 4.0.5.0.C.W.) TO 1	IBM_TDB	2002/02/05 10:12
-	2	("6040596").PN.	USPAT;	2003/03/05 10:12
			US-PGPUB;	!
	1		EPO; JPO;	
4 1 1			DERWENT;	}
			IBM_TDB	<u> </u>